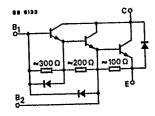
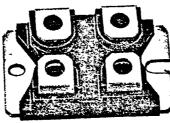




Terminal connections

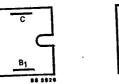


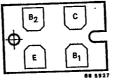
T1.2/1997.0888 E 2796 D-05



TFK 3080 DA

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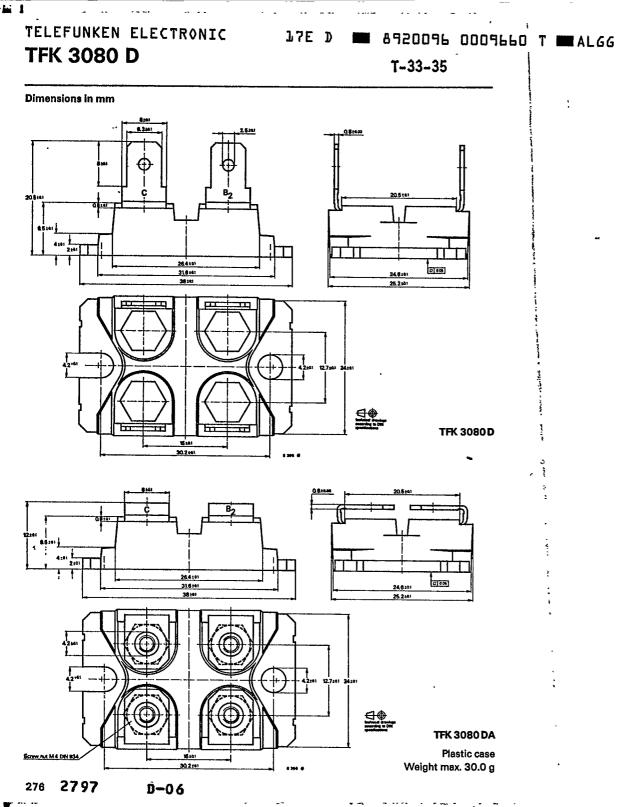




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Absolute maximum fatings				v			Į	
Collector-emitter voltage	V _{CEO} V _{CES}		1000 1000	v v				
- Emitter-base voltage	V _{EBO}		8	V A				
Collector current	l _c		30	A				
Collector peak current	I _{CM}		60	А А		1		
Base current	l _B		2			1		
Base peak current	I _{BM}		4	A			_	
Total power dissipation $T_{case} \leq 25 \ $	P _{tot}		275 150	۷۷ مر			-	
Junction temperature	T _I		-40+150	9				
Storage temperature range	T _{stg}		2500		- -			
Insulation voltage	V _{is}		2500		•	1		
Maximum thermal resistances Junction case			0.45	кл	N			
Power transistor	R _{thJC}		1.5	ĸ٨	N	1		
Free-wheel diode	R _{thJC}					1		
Characteristics T _{case} ≖ 25 °C, unless otherwise specified		Min.	Тур.	Max.				
Collector cut-off current V _{CE} = 1000 V V _{CE} = 1000 V	I _{ces} I _{ceo}			1.0 m 1.0 m		, ; ;		
Emitter cut-off current V _{EB} = 8 V	I _{EBO}			200 n	nA	-		
Collector-emitter breakdown voltage $I_c = 1 \text{ A}, L = 125 \text{ mH}$	V _{(BR)CEO}	1000			V			
Emitter-base breakdown voltage / _E ==0,5 A	V _{(BR)EBO}	8			۷			
Collector saturation voltage $I_c = 30 \text{ A}, I_B = 0.6 \text{ A}$	V _{CEsat}			2.5	V	4		
Base saturation voltage $I_c = 30 \text{ A}, I_B = 0.6 \text{ A}$	V _{BEsat}			3.5	v			

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<u>,</u>		Min.	Тур.	Max.			ł	
Collector-emitter working voltage I _{CWoff} = 48 A,I _{B1} = 1.4 A, - <i>I_{B2}</i> = 2 A Forward voltage of the diode	V _{CEW}	800			v	and the physical first and		
/ _F = 30 A	V _F			1.8	V	į		
Switching characteristics						1		
Inductive load, 7 _{case} == 100 °C						•		
$I_{\rm C} = 30$ A, $I_{\rm B1} = 0.6$ A, $-I_{B2} = 2$ A						÷	-	
Storage time	t _s			15	μs	4		
Fall time	t _f			3	hs			
Prot 250 W 200	3		Case = 25 ℃	100 mA 80 80 80 80				
				40 mA 20 m		ւ ու ունեստեստեր		
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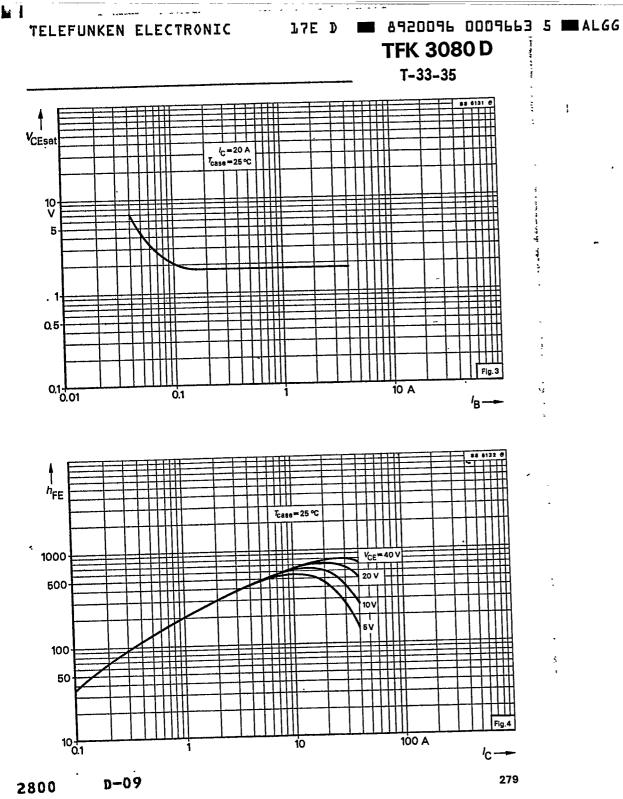
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Family of curves

Besides the static (d. c.) and dynamic (a. c.) characteristics, family of curves are given for specified operating conditions. They show the typical interdepedence of individual characteristics. Partly are given the scattering limits. They signify that at least 95% of the delivery lies inside these tolerances.

6.6. Additional informations

Preliminary specifications

This heading indicates that some information on the device concerned may be subject to slight changes.

Not for new developments

This heading indicates that the device concerned should not be used in equipment under development, it is, however, available for present production.

7. Taping and reeling

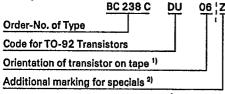
7.1. Taping of TO-92 transistors

Standard reeling: Taped on reel, reeled together with a paper film.

7.1.1. Order Numbers

Add the taping-code to the order number.

Example:



¹⁾ 06 = View on flat side of transistor, view on gummed tape

05 = View on round side of transistor, view on gummed tape

²⁾ Additional marking "O" :

Taping without paper film

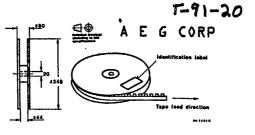
Additional marking "Z":

Zigzag folded tape inspecial box. Marking for orientation of transistor not necessary, because box can be opened on top or botton.

Example for order No.: BC 237 C DU Z

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8920096 0009380 4 🛲 ALGG

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Fig. 7.1. Dimensions of reel in mm

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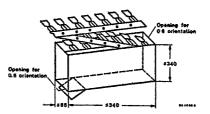


Fig. 7.2. Dimension of box for Zigzag folding in mm

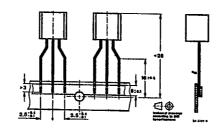


Fig. 7.3. Dimensions of tape in mm

7.1.2 Quantity of devices

1 000 devices per reel

2000 devices per folded tape in special box.

7.2 Taped transistors in SOT 23 and SOT 143 case

a) Standard taping

Designation is attached with code GS 08 in case of standard taping. Example for normal version transistors as standard taped: BF 569-GS08.

Example for R-version transistors as standard taped: BF 569 R-GS 08.

In case of standard taping, the transistor orientation on the tape is shown in Fig. 7.4 and Fig. 7.5.

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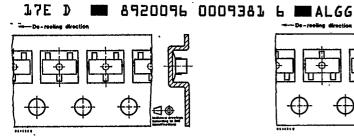


Fig. 7.4 Standard taped SOT 23

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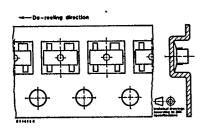


Fig. 7.5 Standard taped SOT 143

- b) Reverse taping
 - Desigantion is attached with code GS 07 in case of reverse taping. Example for normal version transistors as reverse taped: BF 569 R-GS 07. Example for R-version transistors as reverse taping: BF 569 R-GS 07.

In case of reverse taping, the transistor orientation on the tape is shown in Fig. 6. Regarding MOF-FET and MES-FET devices, reverse

taping is at present not available.

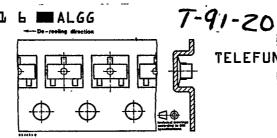


Fig. 7.6 Reverse taped SOT 23

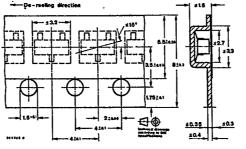


Fig. 7.7 Dimensions of tape in mm

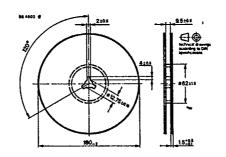


Fig. 7.8 Dimensions of reel in mm

		7.2.2 Quantity of devices					
8. Asses	sories		3000 devices per reel				
Number	Fig.	Designation	For case				
	-	•					
119880	8.1.	Isolating washer thickness 60 µm	12A 3 DIN 41869				
			JEDEC TO 126 (SOT 32)				
564542	8.2.	Isolating washer thickness 50 µm	14A 3 DIN 41 869				
			JEDEC TO 220 (SOT 78)				
912884	8.3	Isolating washer thickness 50 µm	15A 3 DIN 41 869				
			(TOP3) for clip mounting				
191131	8.4	Isolating washer thickness 50 µm	15A 3 DIN 41 869				
			(TOP3) for screw mounting				
191 140	8.5	Mounting clip	15A 3 DIN 41869				
101140	0.0	mounting only	(TOP3)				
560524	00	Indiating weather thickness 100 up at 50 up					
569524	8.6	lsolating washer thickness 100 μm + 50 μm					
			JEDEC TO 3				
			Devices with high reverse voltage				

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